

# SEMITOP<sup>®</sup> 2

## **IGBT** Module

### SK15GH063

Preliminary Data

## Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchtrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63 532

## **Typical Applications\***

• Switching (not for linear use)

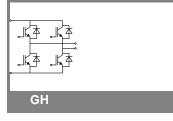
Inverter

Switched mode power supplies

• UPS

Absolut	e Maximum Ratings	Ts	= 25 °C, unless otherwise s	pecified	
Symbol	Conditions		Values		
IGBT					
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		600	V	
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	20	Α	
		T <sub>s</sub> = 80 °C	14	А	
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		30	А	
V <sub>GES</sub>			± 20	V	
t <sub>psc</sub>	$\label{eq:V_CC} \begin{split} V_{CC} &= 300 \text{ V};        $	T <sub>j</sub> = 125 °C	10	μs	
Inverse	Diode		•		
I <sub>F</sub>	T <sub>j</sub> = 150 °C	T <sub>s</sub> = 25 °C	20	А	
		T <sub>s</sub> = 80 °C	15	А	
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		28	А	
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave	T <sub>j</sub> = 150 °C	100	А	
Module					
I <sub>t(RMS)</sub>				А	
T <sub>vj</sub>			-40 +150	°C	
T <sub>stg</sub>			-40 +125	°C	
V <sub>isol</sub>	AC, 1 min.		2500	V	

Characteristics T <sub>s</sub> =			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 0.4 \text{ mA}$		4,5	5,5	6,5	V	
I <sub>CES</sub>	$V_{GE}$ = 0 V, $V_{CE}$ = $V_{CES}$	T <sub>j</sub> = 25 °C			0,05	mA	
		T <sub>j</sub> = 125 °C				mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 20 V	T <sub>j</sub> = 25 °C			120	nA	
		T <sub>j</sub> = 125 °C				nA	
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1,2		V	
		T <sub>j</sub> = 125 °C		1		V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		53		mΩ	
		T <sub>j</sub> = 125°C				mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 15 A, V <sub>GE</sub> = 15 V			2	2,5	V	
		T <sub>j</sub> = 125°C <sub>chiplev.</sub>				V	
Cies				0,8		nF	
C <sub>oes</sub>	$V_{CE}$ = 25, $V_{GE}$ = 0 V	f = 1 MHz				nF	
C <sub>res</sub>				0,06		nF	
t <sub>d(on)</sub>				35		ns	
t <sub>r</sub>	$R_{Gon}$ = 68 $\Omega$	V <sub>CC</sub> = 300V		50		ns	
E <sub>on</sub>	<b>D</b> 00.0	I <sub>C</sub> = 15A		0,71		mJ	
t <sub>d(off)</sub>	$R_{Goff} = 68 \Omega$	$T_j = 125 °C$		250		ns	
t <sub>f</sub>		V <sub>GE</sub> =±15V		20		ns	
E <sub>off</sub>				0,4		mJ	
R <sub>th(j-s)</sub>	per IGBT				1,9	K/W	





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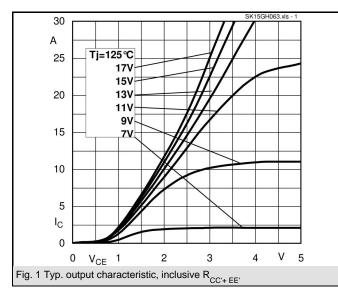
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- Inverter
- Switched mode power supplies
- UPS

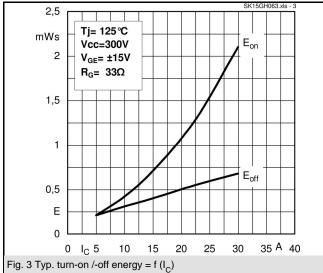
Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse D	oide						
$V_F = V_{EC}$	I <sub>Fnom</sub> = 10 A; V <sub>GE</sub> = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		1,45	1,7	V	
		T <sub>j</sub> = 125 °C <sub>chiplev.</sub>		1,4	1,7	V	
V <sub>F0</sub>		T <sub>j</sub> = 125 °C		0,85	0,9	V	
r <sub>F</sub>		T <sub>j</sub> = 125 °C		55	80	mΩ	
I <sub>RRM</sub>	I <sub>F</sub> = 10 A	T <sub>i</sub> = 125 °C		13		А	
Q <sub>rr</sub>	di/dt = -200 A/µs	,		1,5		μC	
E <sub>rr</sub>	V <sub>CC</sub> = 300V			0,45		mJ	
R <sub>th(j-s)D</sub>	per diode				1,2	K/W	
M <sub>s</sub>	to heat sink M1				2	Nm	
w				19		g	

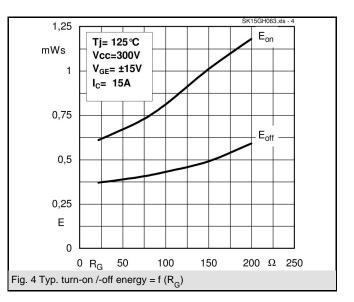
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

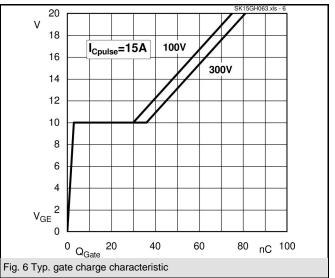
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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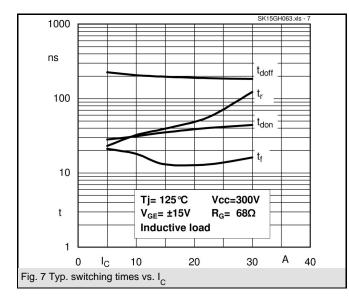


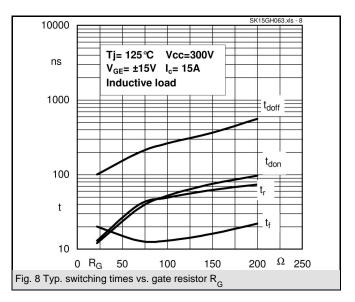


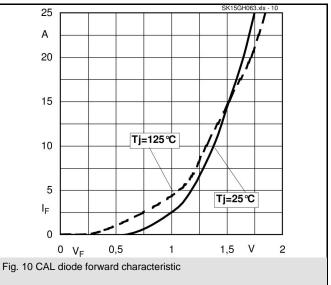


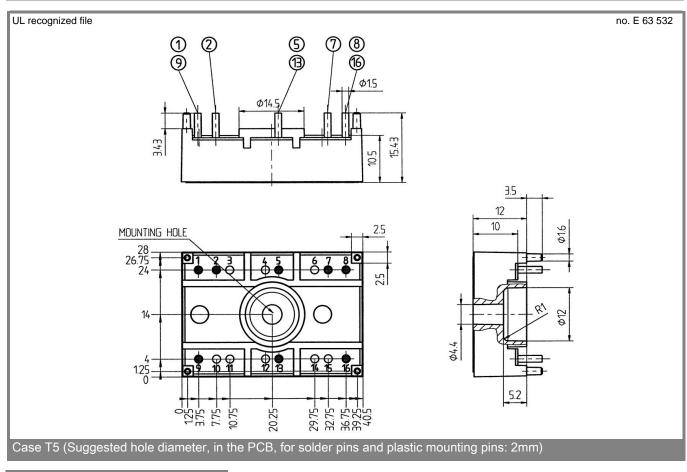
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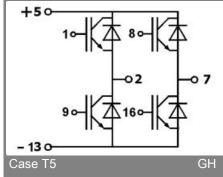
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